Product data sheet

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) module in WeEnPACK-20mm (TO-240AA) for use in applications requiring high blocking voltage capability, high inrush current capability and high thermal cycling performance

2. Features and benefits

- · High blocking voltage capability
- High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability
- Package meets UL certification
- Package is RoHS compliant
- · Industry standard outline
- · Soldering pins for PCB mounting
- Copper base plate
- · Cathode Kelvin contacts provided
- UL1557 certified (Document number E346397)

3. Applications

- Softstart AC motor control
- DC Motor control
- AC power control
- Power converter
- Temperature control
- Lighting control

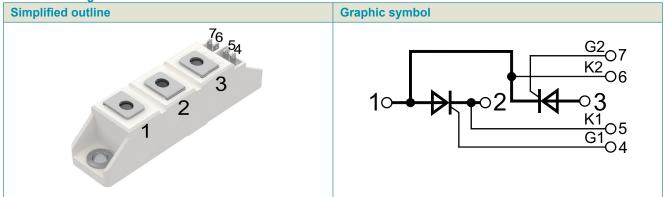
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes		Values		Unit		
Absolute maximum rating									
V_{DRM}	repetitive peak forward voltage				1600		V		
V_{RRM}	repetitive peak reverse voltage				1600		V		
I _{T(RMS)}	RMS on-state current	half sine wave			182		Α		
I _{TSM}	non-repetitive peak on-	half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 10 \text{ ms}$		2300			Α		
	state current	half sine wave; $T_{j(init)} = 130 ^{\circ}\text{C}$; $t_p = 10 \text{ms}$			2000		Α		
		half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 8.3 \text{ ms}$		2530			Α		
		half sine wave; $T_{j(init)} = 130 ^{\circ}\text{C}$; $t_p = 8.3 \text{ms}$			2200		Α		
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit		
Static characteristics									
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C}$		30	-	100	mA		
$V_{\rm GT}$	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C		-	0.75	1.2	V		
V _T	on-state voltage	I _T = 116 A; T _j = 25 °C		-	-	1.29	V		

5. Pinning information

Table 2. Pinning information



6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WTMH116T16R	WeEnPACK-20mm	WTMH116T16RT	Tray	12	WeEnPACK- 20mmPHB-C	26-Jun-2023

7. Marking

Table 4. Marking codes

Type number	Marking codes
WTMH116T16R	WTMH116T16R

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{DRM}	repetitive peak forward voltage			1600	V
V_{RRM}	repetitive peak reverse voltage			1600	V
I _{T(AV)}	average on-state current	half sine wave		116	Α
I _{T(RMS)}	RMS on-state current	half sine wave		182	Α
I _{TSM}	non-repetitive peak on-state	half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 10 \text{ ms}$		2300	Α
	current	half sine wave; $T_{j(init)} = 130 ^{\circ}C$; $t_p = 10 ms$		2000	Α
		half sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 8.3 ms$		2530	Α
		half sine wave; $T_{j(init)} = 130 ^{\circ}C$; $t_p = 8.3 ms$		2200	А
l ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse		26.4	kA²s
dl _⊤ /dt	rate of rise of on-state current	$I_G = 200 \text{ mA}; T_j = 130 \text{ °C}$		200	A/µs
I _{GM}	peak gate current			10	А
V_{RGM}	peak reverse gate voltage			5	V
P_GM	peak gate power			20	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period		0.5	W
T _{stg}	storage temperature			-40 to 130	°C
T _j	junction temperature			-40 to 150	°C

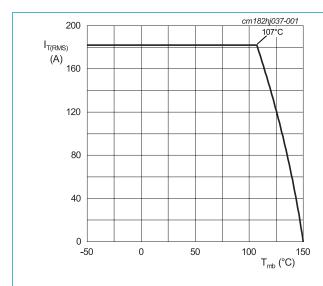
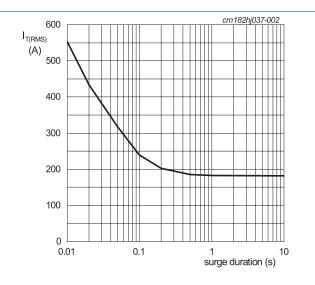


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



 $f = 50 \text{ Hz}; T_{mb} = 107 \text{ }^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

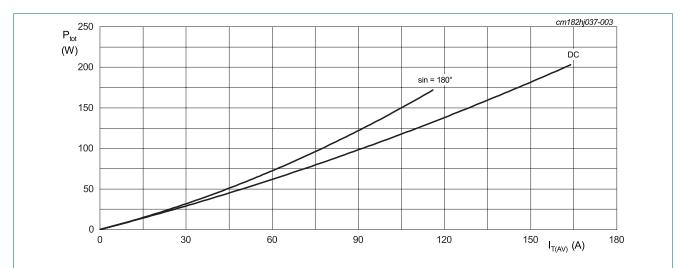
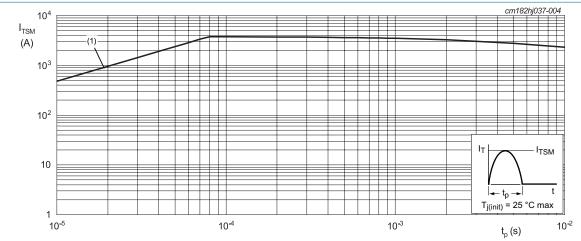


Fig. 3. Total power dissipation as a function of average on-state current; maximum values; per thyristor



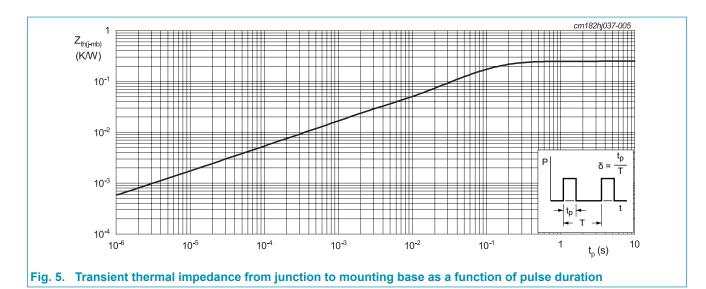
 $t_p \le 10 \text{ ms}$ (1) $dI_T/dt \text{ limit}$

Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-c)}	thermal resistance from junction to case	per thyristor	-	-	0.25	K/W
		per module	-	-	0.125	K/W
R _{th(j-h)}	thermal resistance from junction to heatsink	per thyristor	-	-	0.48	K/W
		per module	-	-	0.24	K/W



10. Package characteristics

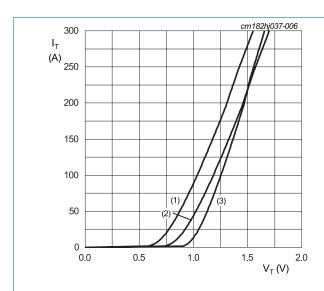
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol}	isolation voltage	50/60 Hz; RMS; $I_{ISOL} \le 1$ mA; t = 1 second; AC	-	-	3600	V
		50/60 Hz; RMS; I _{ISOL} ≤ 1 mA; t = 1 minute; AC	-	-	3000	V

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics		, , , , , , , , , , , , , , , , , , ,			
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C	30	-	100	mA
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T_j = 25 ^{\circ}\text{C}$	-	0.75	1.2	V
		$V_D = 2/3 V_{DRM}$; $I_T = 0.1 A$; $T_j = 130 °C$	0.25	0.4	-	V
I_{GD}	gate non-trigger current	T _j = 130 °C	-	-	8	mA
V_{GD}	gate non-trigger voltage	T _j = 130 °C	-	-	0.2	V
I _L	latching current	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C	-	-	300	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C	-	-	200	mA
V _T on-sta	on-state voltage	I _T = 116 A; T _j = 25 °C	-	-	1.29	V
		I _T = 300 A; T _j = 25 °C	-	-	1.65	V
V _{TO}	threshold voltage	T _j = 130 °C	-	-	0.9	V
r _T	slope resistance	T _j = 130 °C	-	-	2.0	mΩ
I _D	off-state current	V _D = 1600 V; T _j = 25 °C	-	-	100	μΑ
		V _D = 1600 V; Tj = 130 °C	-	2	10	mA
		V _D = 1600 V; T _j = 150 °C	-	10	-	mA
I _R	reverse current	V _R = 1600 V; T _j = 25 °C	-	-	100	μΑ
		V _R = 1600 V; Tj = 130 °C	-	2	10	mA
		V _R = 1600 V; T _j = 150 °C	-	10	-	mA
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 1072 V; T_j = 130 °C; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; gate open circuit	1500	-	-	V/µs
t _{gt}	gate-controlled turn-on time	$I_{TM} = 40 \text{ A}; V_D = 800 \text{ V}; I_G = 100 \text{ mA};$ $(dI_G/dt)_M = 1 \text{ A}/\mu\text{s}; T_j = 25 ^{\circ}\text{C}$	-	2	-	μs



 $V_{TO} = 0.9 \text{ V}; r_T = 0.002 \Omega$

(1) $T_j = 130$ °C; typical values

(2) $T_j = 130 \,^{\circ}\text{C}$; maximum values (3) $T_i = 25 \,^{\circ}\text{C}$; maximum values

Fig. 6. On-state current as a function of on-state voltage

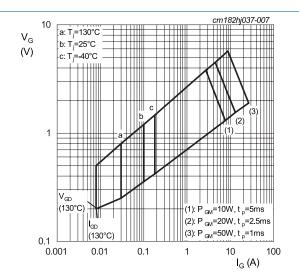
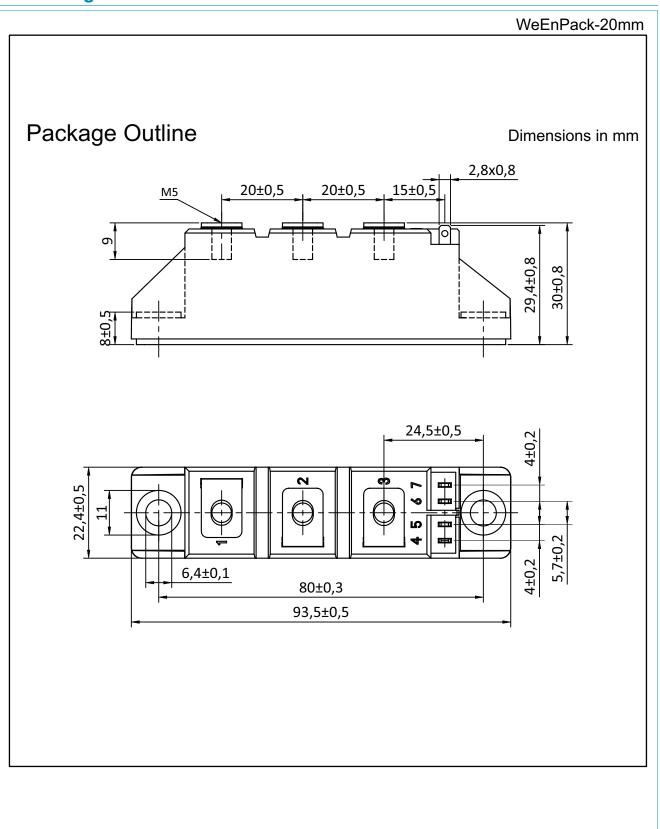


Fig. 7. Gate voltage as a function of gate current

12. Package outline



13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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WTMH116T16R

SCR Module

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